

Abstract of the Disclosure**A Lateral Thyristor Structure for Protection Against Electrostatic Discharge**

To protect against electrostatic discharges in monolithic integrated circuits in CMOS technology, a lateral thyristor structure is presented which has a much lower firing voltage compared to conventional thyristor structures.

Figure 3

List of Reference Symbols

1	Supply connection
2	Supply connection
3	Input/output
4	Interior circuit
5	Clamping circuit
6	Clamping circuit
7	Diode
8	Connecting line
9	Resistor
10	Weakly p-doped semiconductor substrate
11	Weakly n-doped well region
12	Strongly n-doped region
13	Strongly p-doped region
14	Strongly n-doped region
15	Field oxide region
16	Cathode
17	Anode
18	Field oxide region
20	Weakly p-doped semiconductor substrate
21	Weakly n-doped well region
22	Strongly n-doped region
23	Strongly p-doped region
24	Strongly n-doped region
25	Strongly n-doped region
26	Cathode
27	Anode
28	Field oxide region
29	Field oxide region
30	Field oxide region
21'	Weakly n-doped well region
22'	Strongly n-doped region
23'	Strongly p-doped region
24'	Strongly n-doped region
25'	Strongly n-doped region

27'	Anode
28'	Field oxide region
29'	Field oxide region
30'	Field oxide region
31	Substrate contact ring
32	Terminal
40	Internal connection
41	Strongly n-doped region
42	Thyristor